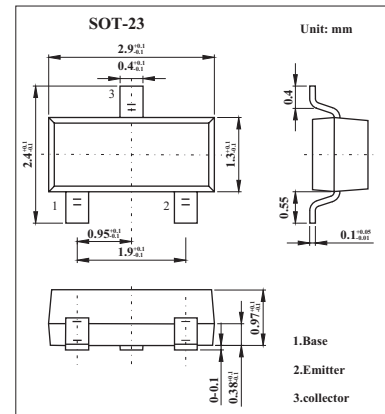


PNP General Purpose Transistors

BCX17,BCX18

■ Features

- Low current (max. 100 mA).
- Low voltage (max. 32 V).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	BCX17	BCX18	Unit
Collector-base voltage	V_{CB0}	-50	-30	V
Collector-emitter voltage	V_{CEO}	-45	-25	V
Emitter-base voltage	V_{EBO}	-5		V
Collector current	I_C	-500		mA
Peak collector current	I_{CM}	-1000		mA
Peak base current	I_{BM}	-200		mA
Total power dissipation *	P_{tot}	250		mW
Storage temperature	T_{stg}	-65 to +150		$^\circ\text{C}$
Junction temperature	T_j	150		$^\circ\text{C}$
Operating ambient temperature	R_{amb}	-65 to +150		$^\circ\text{C}$
Thermal resistance from junction to ambient *	R_{th-j-a}	500		K/W

* Transistor mounted on an FR4 printed-circuit board.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$I_E = 0; V_{CB} = -20\text{ V}$			-100	nA
	I_{CBO}	$I_E = 0; V_{CB} = -20\text{ V}; T_j = 100\text{ }^\circ\text{C}$			-5	μA
Emitter cutoff current	I_{EBO}	$I_C = 0; V_{EB} = -5\text{ V}$			-100	nA
DC current gain	h_{FE}	$I_C = -100\text{ mA}; V_{CE} = -1\text{ V}$	100		600	
		$I_C = -300\text{ mA}; V_{CE} = -1\text{ V}$	70			
		$I_C = -500\text{ mA}; V_{CE} = -1\text{ V}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$			-620	mV
Base to emitter voltage	V_{BE}	$I_C = -500\text{ mA}; V_{CE} = -1\text{ V}$			-1.2	V
Collector capacitance	C_C	$I_E = I_C = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$		9		pF
Transition frequency	f_T	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	80			MHz

■ h_{FE} Classification

TYPE	BCX17	BCX18
Marking	T1	T2